

SA56-11EWA-SBI

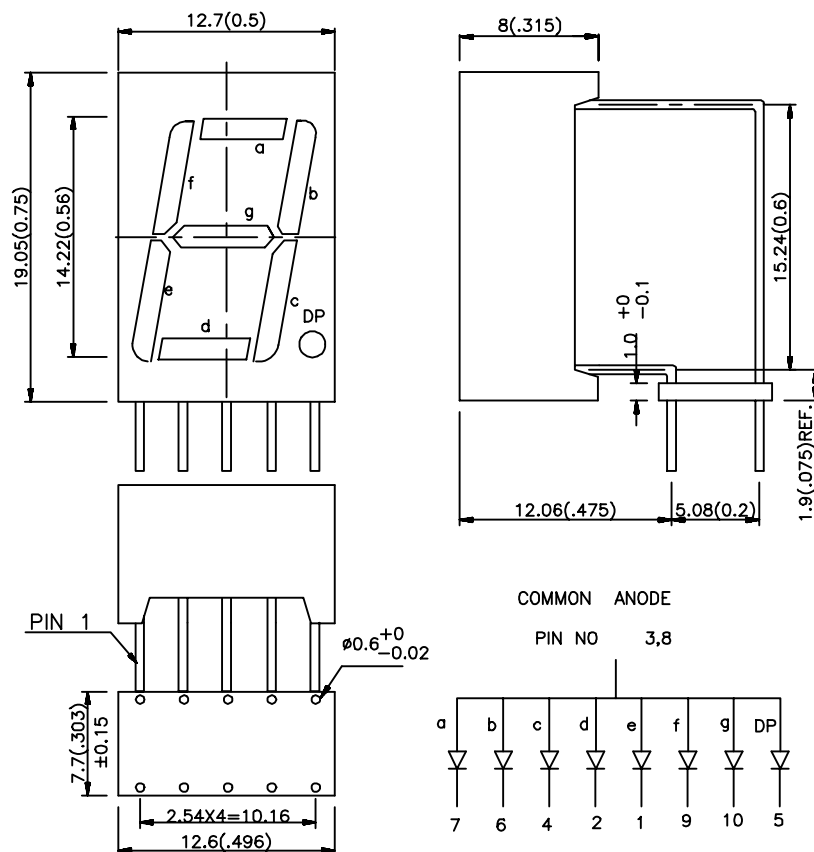
Features

- 0.56 INCH DIGIT HEIGHT.
- LOW CURRENT OPERATION.
- EXCELLENT CHARACTER APPEARANCE.
- EASY MOUNTING ON P.C. BOARDS OR SOCKETS.
- I.C. COMPATIBLE.
- MECHANICALLY RUGGED.
- STANDARD : GRAY FACE, WHITE SEGMENT.

Description

The High Efficiency Red source color devices are made with Gallium Arsenide Phosphide on Gallium Phosphide Orange Light Emitting Diode.

Package Dimensions & Internal Circuit Diagram



Notes:

1. All dimensions are in millimeters (inches), Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.
2. Specifications are subjected to change without notice.

Selection Guide

Part No.	Dice	Iv (ucd) @ 10 mA		Description
		Min.	Typ.	
SA56-11EWA-SBI	HIGH EFFICIENCY RED (GaAsP/GaP)	1900	6400	Common Anode

Electrical / Optical Characteristics at T_A=25°C

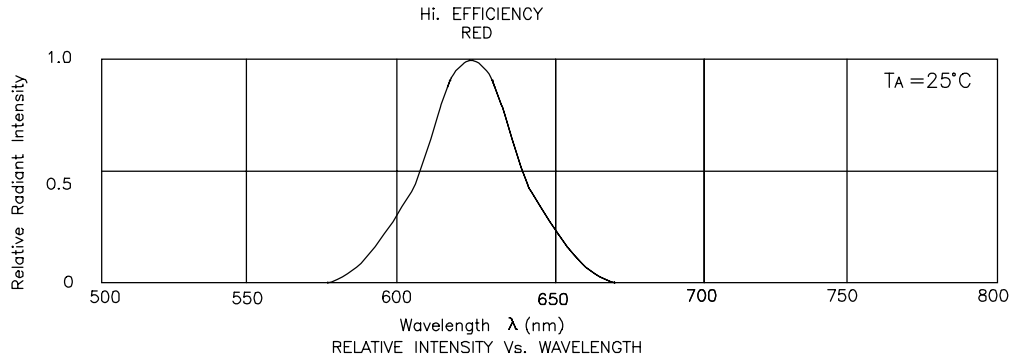
Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
λ_{peak}	Peak Wavelength	High Efficiency Red	625		nm	IF=20mA
$\Delta\lambda_{1/2}$	Spectral Line Halfwidth	High Efficiency Red	45		nm	IF=20mA
C	Capacitance	High Efficiency Red	45		pF	VF=0V;f=1MHz
V _F	Forward Voltage	High Efficiency Red	2.0	2.5	V	IF=20mA
I _R	Reverse Current	All		10	uA	VR = 5V

Absolute Maximum Ratings at T_A=25°C

Parameter	High Efficiency Red	Units
Power dissipation	105	mW
DC Forward Current	30	mA
Peak Forward Current [1]	150	mA
Reverse Voltage	5	V
Operation/Storage Temperature	-40°C To +85°C	
Lead Solder Temperature [2]	260°C For 5 Seconds	

Notes:

- 1/10 Duty Cycle, 0.1ms Pulse Width.
- 4mm below package base.



High Efficiency Red SA56-11EWA-SBI

